			All
	Application No.	Applicant(s)	
	10/698,260	SRIDEVAN, SRIKAN	Τ
Notice of Allowability	Examiner	Art Unit	
	Thinh T. Nguyen	2818	
The MAILING DATE of this communication ap All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL-8 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.3	IS (OR REMAINS) CLOSED 35) or other appropriate common RIGHTS. This application is	in this application. If not included nunication will be mailed in due c	d ourse. THIS
1. X This communication is responsive to 10/31/2003.			
2. \boxtimes The allowed claim(s) is/are <u>1-11</u> .			
3. $igotimes$ The drawings filed on <u>31 October 2003</u> are accepted by	the Examiner.		
4. Acknowledgment is made of a claim for foreign priority a) All b) Some* c) None of the: 1. Certified copies of the priority documents had 2. Certified copies of the priority documents had 3. Copies of the certified copies of the priority International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DAT noted below. Failure to timely comply will result in ABANDOI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be sull INFORMAL PATENT APPLICATION (PTO-152) which go the including changes required by the Notice of Draftsperior (a) including changes required by the Notice of Draftsperior (b) including changes required by the attached Examin Paper No./Mail Date (b) Including changes required by the attached Examin Paper No./Mail Date Identifying indicia such as the application number (see 37 CFF each sheet. Replacement sheet(s) should be labeled as such in the deattached Examiner's comment regarding REQUIREMENT.	ave been received. ave been received in Application documents have been received. E" of this communication to fill NMENT of this application. bmitted. Note the attached Exgives reason(s) why the oath of the submitted. erson's Patent Drawing Review. er's Amendment / Comment of the header according to 37 Caposit of BIOLOGICAL MATERIAL Application.	con No ed in this national stage application in this national stage application is a reply complying with the requirement of the drawings in the front (not the IFR 1.121(d). TERIAL must be submitted. No	uirements OTICE OF back) of
Attachment(s)	F □ Notice of I	nformal Patent Application (PTO	152\
 Notice of References Cited (PTO-892) Notice of Draftperson's Patent Drawing Review (PTO-94) 		nformal Patent Application (PTO Summary (PTO-413),	-102)
2. ☐ Notice of Draitperson's Patent Drawing Review (PTO-94)	Paper No	./Mail Dates s Amendment/Comment	
Paper No./Mail Date	,		
4. Examiner's Comment Regarding Requirement for Depos	·)	s Statement of Reasons for Allov	vance
of Biological Material	9. ☐ Other	·	
Davish (- · · · · · · · · · · · · · · · · · · ·		
Supervisory Pate Technology Ce			

Application/Control Number: 10/698,260

Art Unit: 2818

DETAILED ACTION

Specification

1. The specification has been checked to the extent necessary to determine the presence of all possible minor errors. However, the applicant cooperation is requested in correcting any errors of which the applicant may become aware in the specification.

Reason for allowance

- 2. Claims 1-11 arte allowed. The following is an examiner's statement of reason for allowance: None of the references of record teaches or suggests the claimed ***

 SEMICONDUCTOR DEVICE having the limitations:
 - --"a silicon carbide semiconductor die consists of one of a junction field effect transistor and a metal semiconductor field effect transistor, the silicon carbide semiconductor die having three electrodes including a source electrode, a gate electrode and a drain electrode, each of the three electrodes being on one of a top surface and a bottom surface of the silicon carbide die and the drain electrode being electrically connected to the drain contact; and a silicon metal oxide semiconductor field effect transistor comprising a

doped silicon substrate and three electrodes including a source electrodes

Application/Control Number: 10/698,260

Art Unit: 2818

a gate electrode and a drain electrode, each of the three electrodes being on one of an upper surface and a lower surface of the silicon transistor, the gate electrode of the silicon transistor being electrically connected to the gate contact, the drain electrode of the silicon transistor being electrically connected with the source electrode of the silicon carbide die and the source electrode of the silicon transistor being electrically connected to both the source contact and the gate electrode of the silicon carbide die; "--

and all other limitations as recited in claim 1.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Pankove (US patent 6,169,330) discloses a method an apparatus for packaging high temperature solid state electronics device; Parson et al. (US patent Application Publication US 2002/066903 A1 disclose an adhesion and /or encapsulation of silicon carbide based semiconductor device on ceramic substrates.

Application/Control Number: 10/698,260

Art Unit: 2818

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thinh T Nguyen whose telephone number is 571-272-1790. The examiner can normally be reached on Monday-Friday 9:00am-6:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached at 571-272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Thinh T Nguyen

Art unit 2818

David Nelms
Supervisory Patent Examiner
Technology Center 2800